

# C O N T E N T S

PREFACE		i-vii
CHAPTER I	INTRODUCTION	
1.1	Semiconductors with shallow and deep level impurities.	1
1.2	Kinetics of the recombination processes in semiconductors.	5
1.2.1	Carrier lifetime.	6
1.2.2	Minority carrier lifetime.	7
1.2.3	Band-to-band recombination.	8
1.2.4	Recombination and generation through deep impurities.	9
1.2.4.1	Uniform injection.	14
1.2.4.2	Low level injection.	15
1.2.4.3	High level injection.	16
1.2.5	Auger recombination.	16
1.3	Thermodynamic analysis of deep levels.	17
1.3.1	Non radiative capture at deep levels.	21
1.4	Introduction of deep levels in semiconductors.	23
	References	25
CHAPTER II	EXPERIMENTAL METHODS AND INSTRUMENTATION	
2.1	Capacitance-Voltage (C-V) characteristics	28
2.1.1	Carrier concentration	29
2.1.2	Built-in potential	30
2.1.3	Barrier height	31
2.1.4	Depth profile	32
2.1.5	Stray capacitance and contact area	34

2.1.6	Charge state	35
2.2	Current-Voltage (I-V) characteristics	36
2.2.1	Forward I-V	36
2.2.2	Ideality factor $n$ and Saturation current $I_s$	36
2.2.3	Barrier height $\phi_{Bn}$	37
2.2.4	Activation energy and electrically active area.	37
2.3	Reverse I-V	38
2.4	Capacitance-voltage (C-V) measurement system	40
2.5	Current-voltage (I-V) measurement system	41
2.6	Isothermal capacitance and current transients	42
2.6.1	Emission transients	46
2.6.2	Capacitance transients	50
2.6.3	Current transients	53
2.6.4	Capture transients	54
2.7	Deep level transient spectroscopy (DLTS)	56
2.7.1	Principle of DLTS	57
2.7.2	Activation energy measurement	59
2.7.3	Capture cross-section measurement	60
2.7.4	Deep level concentration profile	61
2.8	Computer (IBM PC) controlled deep level transient spectroscopy(DLTS) system	62
2.8.1	System description	64
2.8.2	DLTS controller	65
2.8.3	Data acquisition system (DAS)	71
2.8.4	Temperature monitor and control system	73

2.8.5	Sample cryostat	77
2.8.6	Software	78
	References	79

**CHAPTER III                    STUDIES ON PLATINUM RELATED DEEP LEVELS  
IN SILICON AND THEIR PASSIVATION BY  
ATOMIC HYDROGEN**

3.1	Introduction	85
3.2	Sample preparation	89
3.2.1	Diffusion of platinum	89
3.2.2	Sample preparation for DLTS	91
3.3	Experimental results and discussion	92
	<b>HYDROGENATION OF SEMICONDUCTORS</b>	
3.4	Introduction	97
3.4.1	Mechanism of shallow level passivation	99
3.4.2	Mechanism of deep level passivation	99
3.5	Hydrogenation system	101
3.5.1	System used for hydrogenation	103
3.5.2	Hydrogenation procedure	105
3.6	Experimental results and discussion	106
3.6.1	Thermal reactivation of hydrogen passivated platinum deep	106
3.7	Conclusions	109
	References	110

**CHAPTER IV                    STUDIES ON PROCESS INDUCED DEEP LEVELS  
IN SILICON**

4.1	Introduction	114
4.2	Experimental work	119

4.3	Sample preparation for DLTS	122
4.4	Results and discussion	124
4.4.1	Effect of temperature on deep level concentration	125
4.4.2	Effect of ambient on deep level formation	128
4.4.3	Gettering effect of boron on deep levels	127
4.4.4	Gettering effect of phosphorus on deep levels	128
4.4.5	Effect of oxygen flow rate on the phosphorus gettering	129
4.5	Identification of deep levels	129
4.6	Conclusions	132
	References	133

## CHAPTER V

### SUMMARY AND CONCLUSIONS

5.1	Summary	135
5.2	Limitations and shortcomings	138
5.3	Suggestions for future work	139